

SPTECH Silicon PNP Darlington Power Transistor MJH11021

DESCRIPTION

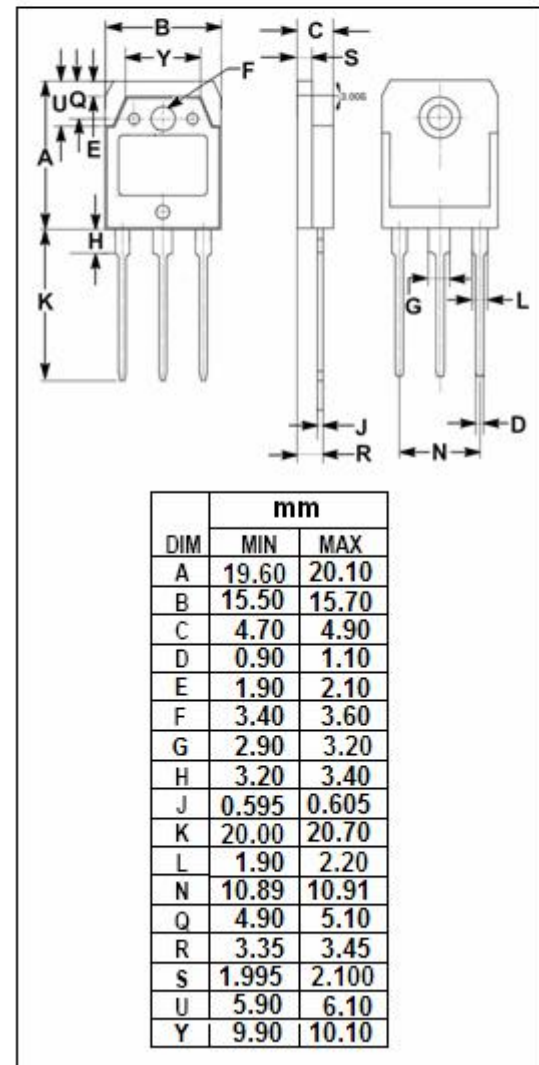
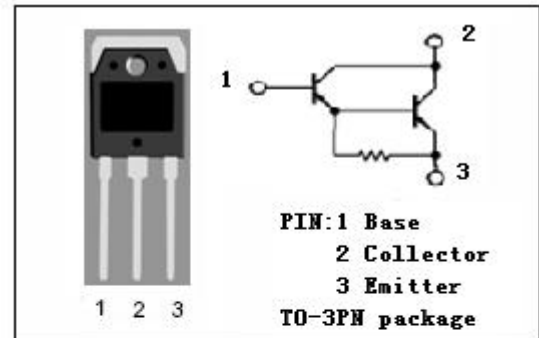
·Collector-Emitter Sustaining Voltage
 : $V_{CEO(SUS)} = -250V$ (Min.) ·High DC
 Current Gain
 : $h_{FE} = 400(\text{Min.}) @ I_C = -10A$ ·Low
 Collector Saturation Voltage
 : $V_{CE(sat)} = -1.0V(\text{Max.}) @ I_C = -5.0A$
 ·Complement to Type MJH11022
 ·Minimum Lot-to-Lot variations for
 robust device
 performance and reliable operation

APPLICATIONS

- Designed for audio, series regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-250	V
V_{CEO}	Collector-Emitter Voltage	-250	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current- Continuous	-0.5	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	150	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS**T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; I _B = 0	-250			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -10A; I _B = -0.1A			-2.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -15A; I _B = -0.15A			-3.8	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -250V; I _E = 0			-0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-2	mA
hFE-1	DC Current Gain	I _C = -10A; V _{CE} = -5V	400		15000	
hFE-2	DC Current Gain	I _C = -15A; V _{CE} = -5V	100			